

In the Claims:

Please cancel claims 47, 48 and 67-69, without prejudice; and amend claims 46, 49, 50 and 51. The status of the claims is as follows:

1-45 (Canceled)

46. (Currently Amended) A method for providing a thin film on a substrate in order to obtain a product, said film being formed by a material, comprising the steps of:

- dispersing said material in said substrate in order to obtain a mixture;
- modeling said mixture;
- conditioning said mixture-

wherein said modeling step comprises a step for forming, on a surface of said mixture, protrusions and recesses, and said conditioning step comprises a step of causing said material to emerge on the surface of said mixture with a higher concentration in regions corresponding to the protrusions, said step of causing said material to emerge comprising the step of smoothing said mixture in order to smooth any surface roughness, said surface roughness comprising said protrusions.

47-48. (Canceled)

49. (Currently Amended) The method according to ~~claim 48~~ claim 46, wherein said smoothing step comprises a step of exposing said mixture to a solvent for the substrate.

50. (Currently Amended) The method according to ~~claim 48~~ claim 46, wherein said smoothing step comprises a step of heating said mixture.

51. (Currently Amended) The method according to ~~claim 48~~ claim 46, comprising a step of treating, chemically and/or by means of any physical treatment, said emerged material in order to modify its intrinsic properties.

52. (Previously Presented) The method according to claim 51, wherein said chemical treatment step comprises a step for coating said emerged material with a protective layer.

53. (Previously Presented) The method according to claim 46, wherein said modeling step comprises a step of etching said mixture.

54. (Previously Presented) The method according to 46, wherein said modeling step comprises a step of pressure molding said mixture.

55. (Previously Presented) The method according to claim 53, wherein said modeling step comprises a step of heating said mixture in order to soften said substrate.

56. (Previously Presented) The method according to claim 46, wherein said modeling step comprises a step of replica molding said mixture.

57. (Previously Presented) The method according to claim 46, wherein said substrate comprises a polymeric mixture.

58. (Previously Presented) The method according to claim 46, wherein said substrate comprises a polymer.

59. (Previously Presented) The method according to claim 58, wherein said polymer comprises polycarbonate.

60. (Previously Presented) The method according to claim 46, wherein said substrate comprises a copolymer.

61. (Previously Presented) The method according to claim 46, wherein said substrate comprises a molecular material.

62. (Previously Presented) The method according to claim 46, wherein said substrate comprises biological molecules.

63. (Previously Presented) The method according to claim 46, wherein said substrate comprises a gel.

64. (Previously Presented) The method according to claim 46, wherein said substrate is an organic material.

65. (Previously Presented) The method according to claim 46, wherein said material is an inorganic material.

66. (Previously Presented) The method according to claim 46, wherein said material is a biological material.

67. (Previously Presented) The method according to claim 46, wherein said substrate is an organic material.

68. (Previously Presented) The method according to claim 46, wherein said material is an inorganic material.

69. (Previously Presented) The method according to claim 46, wherein said material is a biological material.

70. (Previously Presented) The method according to claim 46, wherein said substrate is soluble in a solvent.

71. (Previously Presented) The method according to claim 46, wherein said material is a conducting material and the resulting product is an electrode, said film being a conducting film.

72. (Previously Presented) The method according to claim 71, wherein said conducting material comprises a metal or metallic particles.

73. (Previously Presented) The method according to claim 46, wherein said material is a semiconducting material and the resulting product is an electrode.

74. (Previously Presented) The method according to claim 46, wherein said material is a semiconducting material and the resulting product is an electronic device or photovoltaic cell or light-emitting diode, said film being a semiconducting film.

75. (Previously Presented) The method according to claim 46, wherein said material is a magnetic material and the resulting product is a magnetically readable memory element.

76. (Previously Presented) The method according to claim 71, wherein said magnetically readable memory element is rewritable, said magnetic material being ferromagnetic.

77. (Previously Presented) The method according to claim 46, wherein said material has optical properties and the resulting product is an optically readable memory element.

78. (Previously Presented) The method according to claim 77, wherein said optically readable memory element is rewritable.

79. (Previously Presented) The method according to claim 46, wherein the parameters of temperature and humidity are fixed, wherein said production of the film is regulated by acting on the duration of said conditioning step.

80. (Previously Presented) The method according to claim 46, wherein the parameters of temperature and time are fixed, and wherein said production of the film is regulated by acting on the humidity parameter in said conditioning step.

81. (Previously Presented) The method according to claim 46, wherein the parameters of humidity and time are fixed, and wherein said production of the film is regulated by acting on the temperature parameter in said conditioning step.

82. (Previously Presented) A spatially structured chemical pattern, wherein it is obtained according to the method described in claim 46, said pattern being constituted by said material.

83. (Previously Presented) An electrode, wherein it is obtained: according to the method described in claim 46, said material being a conducting material.

84. (Previously Presented) An electrode, wherein it is obtained according to the method described in claim 46, said material being a semiconducting material.

85. (Previously Presented) The electrode according to claim 83, wherein said conducting material is metallic.

86. (Previously Presented) A magnetically readable memory element, wherein it is obtained according to the method described in claim 46, said material being a magnetic material.

87. (Previously Presented) A magnetically readable memory element according to claim 86, wherein it is rewritable, said magnetic material being ferromagnetic.



88. (Previously Presented) An optically readable memory element, wherein it is obtained according to the method described in claim 46, said material having optical properties.

89. (Previously Presented) An optically readable memory element according to claim 88, wherein it is rewritable.

90. (Previously Presented) The method according to claim 54, wherein said modeling step comprises a step of heating said mixture in order to soften said substrate.